

1700V N-Channel Depletion-Mode Power MOSFET

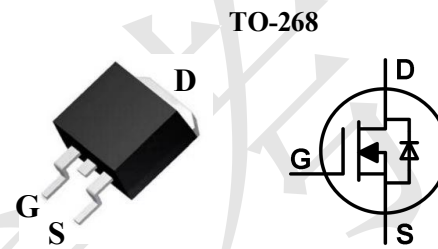
General Features

- Depletion Mode (Normally On)
- Rugged Polysilicon Gate Cell Structure
- Fast Switching Speed
- High Power Density
- RoHS Compliant
- Halogen-free Available

BV_{DSX}	$R_{DS(ON)} (Max.)$	$I_{DSS}(Min)$
1700V	10Ω	2.0A

Applications

- Suppressing Surge Current
- Start-up Circuits
- Converters
- Synchronous Rectification
- Audio Amplifiers
- Constant Current Source
- Ramp Generators
- Current Regulators
- Protection Circuits
- Active Loads



Ordering Information

Part Number	Package	Marking	Remark
DMG23C170A	TO-268	23C170A	Halogen Free

Absolute Maximum Ratings

$T_C=25^{\circ}C$ unless otherwise specified

Symbol	Parameter	DMG23C170A	Unit
V_{DSX}	Drain-to-Source Voltage ^[1]	1700	V
V_{DGX}	Drain-to-Gate Voltage ^[1]	1700	V
P_D	Power Dissipation	560	W
	Derating Factor above 25°C		W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
T_L	Soldering Temperature	300	°C
	Distance of 1.6mm from case for 10 seconds		
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150	

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to the device.